IN THE SPECIFICATION:

*Please insert the following new paragraph after the Title and before the first paragraph on page 1:*

-- This application is the U.S. National Phase under 35 U.S.C. § 371 of International Application No. PCT/JP2005/006080, filed March 30, 2005, which in turn claims the benefit of Japanese Application No. 2004-109791, filed April 2, 2004, the disclosures of which Applications are incorporated by reference herein in their entirety. --

*Please replace the paragraph beginning on page 19, line 23 and ending on page 19, line 27, with the following paragraph:*

Figs. 7A, 7B and 7C show semiconductor lasers 95a, 95b and 95c that are excitation sources of excitation light with the wavelength of 808 nanometers. Furthermore, Figs. 7A, 7B and 7C show excitation light transmitting fibers 77a, 77b and 77c for transmitting excitation light and further show excitation light transmitting fiber cores ~~777d~~ 77d, 77e and 77f.

*Please replace the paragraph beginning on page 22, line 7 and ending on page 22, line 14, with the following paragraph:*

Excitation light entering third waveguide 75 enters filling region 82b of light amplifying fiber 70. Since the refractive indices of outer layer 76 and clad 74 of second waveguide 72 respectively denoted by n76 and n72 satisfy the relation: n76 <

n72, a part of the excitation light is confined in third waveguide 75 and propagates in third waveguide 75 while undergoing multiple reflection. This means that an idle region in which excitation light entering third waveguide 75 propagates and moves to ~~22nd~~ 2nd waveguide 72 and no excitation light is present in third waveguide 75 is provided.